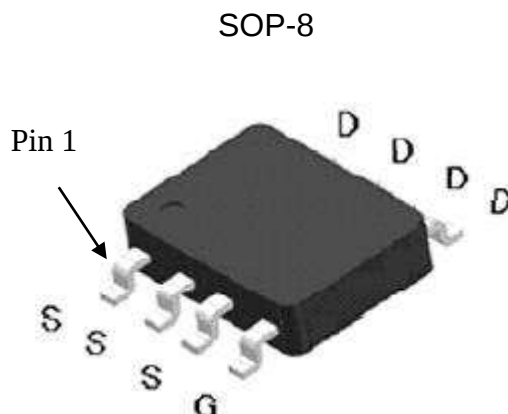


N-Channel Enhancement Mode Power MOSFET

Features:

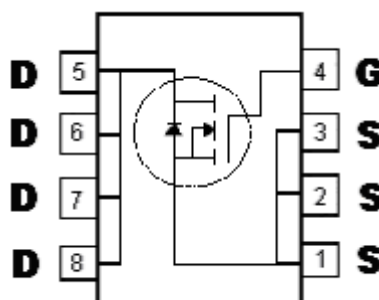
- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Repetitive Avalanche Rated
- Pb-free & Halogen-free package

Outline



BV_{DSS}	100V
I_D @ $T_A=25^\circ\text{C}$, $V_{GS}=10\text{V}$	11.5A
$R_{DS(ON)}$@$V_{GS}=10\text{V}$, $I_D=11.5\text{A}$	9.2 mΩ (typ)
$R_{DS(ON)}$@$V_{GS}=4.5\text{V}$, $I_D=9.5\text{A}$	12.8 mΩ (typ)

Symbol



G : Gate
D : Drain
S : Source

Ordering Information

Device	Package	Shipping
KSCWD011N10RQ8	SOP-8 (RoHS compliant & Halogen-free package)	2500 pcs / Tape & Reel

Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current @ T _A =25°C, V _{GS} =10V	I _D	11.5	A
Continuous Drain Current @ T _A =70°C, V _{GS} =10V		9.2	
Pulsed Drain Current	I _{DM}	46 *1	
Avalanche Current	I _{AS}	11.5	
Avalanche Energy @ L=5mH, I _D =11.5A, V _{DD} =50V	E _{AS}	330	mJ
Repetitive Avalanche Energy @ L=0.05mH	E _{AR}	1.6 *2	
Total Power Dissipation	P _D	T _A =25 °C 3.1	W
		T _A =70 °C 2	
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+150	°C

Note : *1. Pulse width limited by maximum junction temperature

*2. Duty cycle ≤ 1%

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case	R _{th,j-c}	20	°C/W
Thermal Resistance, Junction-to-ambient (Note)	R _{th,j-a}	40	

Note : 40°C / W when mounted on a 1 in² pad of 2 oz copper, t≤10s; 125°C/W when mounted on minimum pad.

Characteristics (Tc=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	100	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	1.2	-	2.6		V _{DS} = V _{GS} , I _D =250μA
G _{FS}	-	16.8	-	S	V _{DS} =10V, I _D =5A
I _{GSS}	-	-	±100	nA	V _{GS} =±20V
I _{DSS}	-	-	1	μA	V _{DS} =80V, V _{GS} =0V
	-	-	25		V _{DS} =80V, V _{GS} =0V, T _j =125°C
*R _{DS(ON)}	-	9.2	12.5	mΩ	V _{GS} =10V, I _D =11.5A
	-	12.8	17		V _{GS} =4.5V, I _D =9.5A
Dynamic					
Qg(V _{GS} =10V) *1, 2	-	54	-	nC	V _{DS} =50V, V _{GS} =10V, I _D =11.5A
Qg(V _{GS} =4.5V) *1, 2	-	27.5	-		
Qgs *1, 2	-	11	-		
Qgd *1, 2	-	12	-		
Ciss	-	2841	-	pF	V _{DS} =25V, V _{GS} =0V, f=1MHz
Coss	-	313	-		
Crss	-	33	-		

Characteristics (Cont. Tc=25°C, unless otherwise specified)

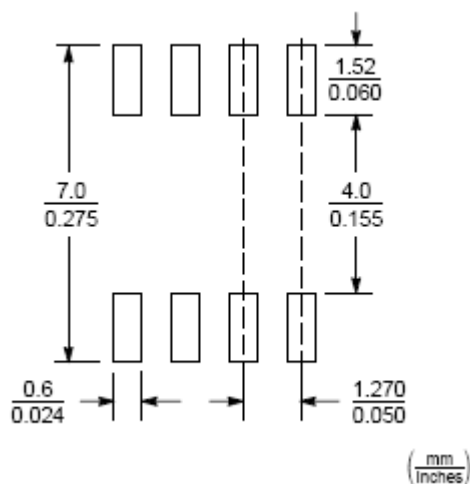
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dynamic					
t _{d(ON)} *1, 2	-	21	-	ns	V _{DS} =50V, I _D =11.5A, V _{GS} =10V, R _{GS} =3Ω
t _r *1, 2	-	18.6	-		
t _{d(OFF)} *1, 2	-	56	-		
t _f *1, 2	-	7	-		
Source-Drain Diode Ratings and Characteristics					
I _S *1	-	-	4	A	
I _{SM} *3	-	-	16		
V _{SD} *1	-	0.71	1	V	I _S =1A, V _{GS} =0V
t _{rr}	-	39	-	ns	I _F =4A, dI _F /dt=100A/μs
Q _{rr}	-	69	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

*2.Independent of operating temperature

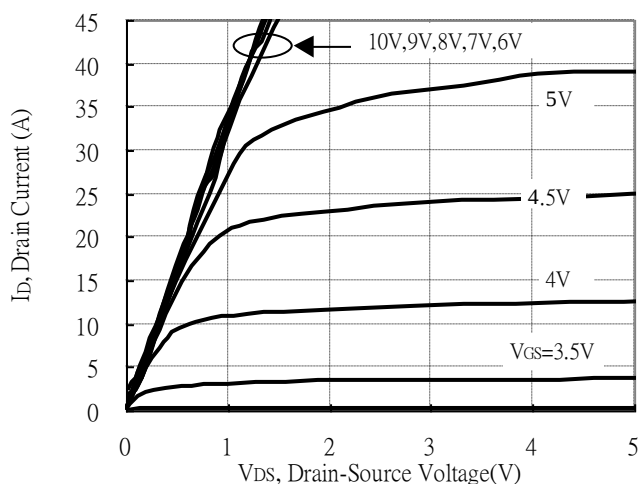
*3.Pulse width limited by maximum junction temperature.

Recommended Soldering Footprint

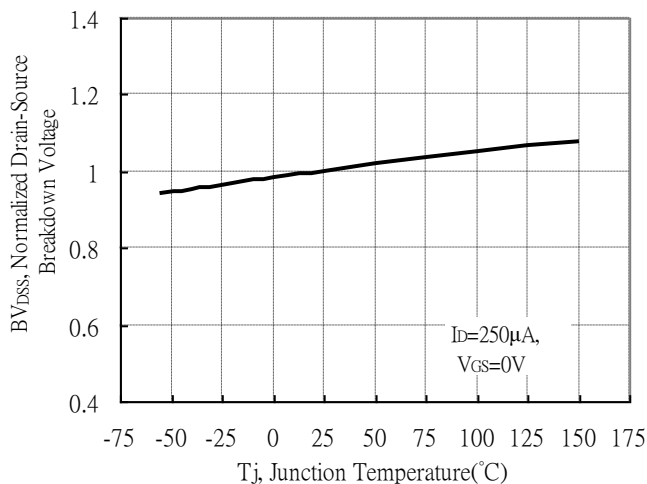


Typical Characteristics

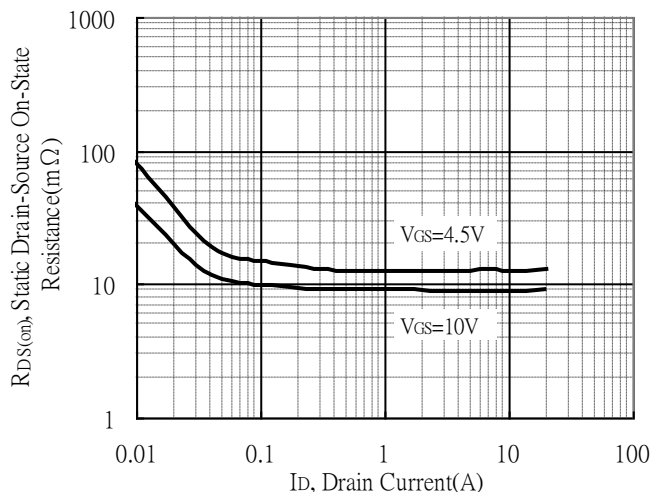
Typical Output Characteristics



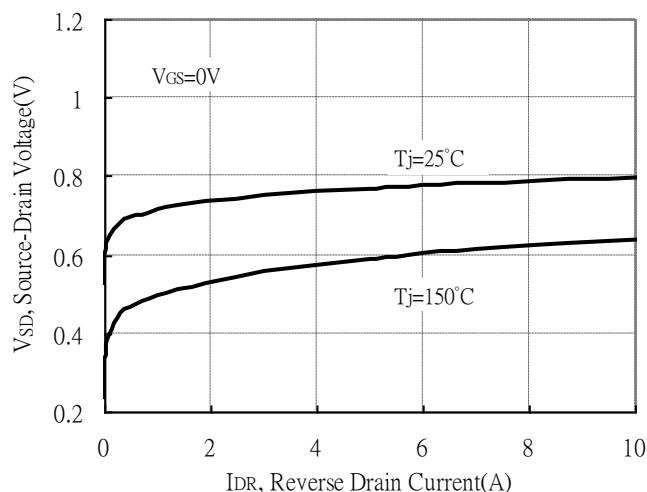
Breakdown Voltage vs Ambient Temperature



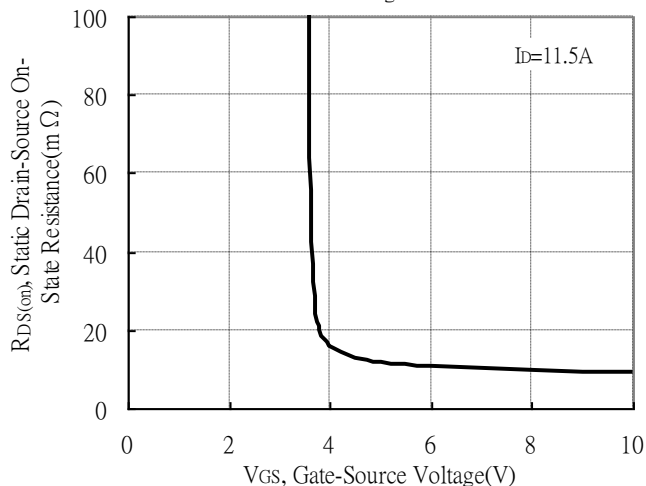
Static Drain-Source On-State resistance vs Drain Current



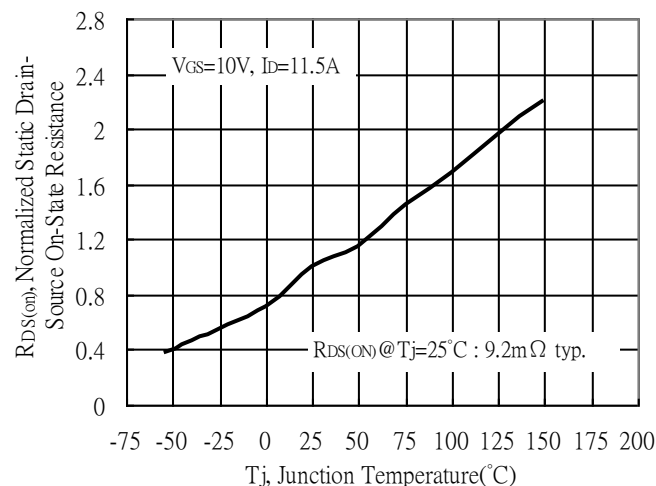
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

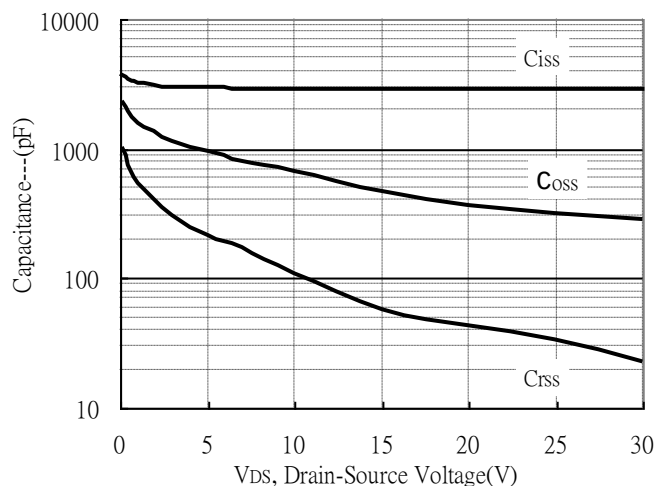


Drain-Source On-State Resistance vs Junction Temperature

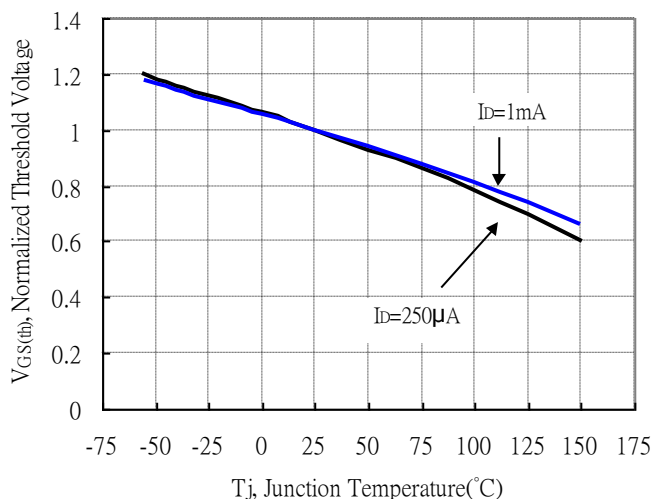


Typical Characteristics(Cont.)

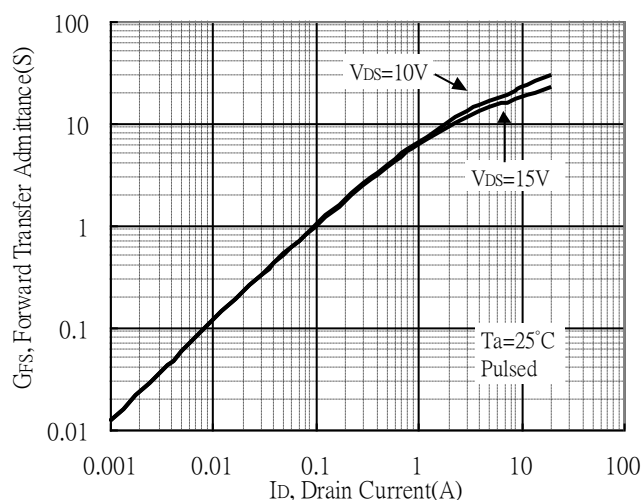
Capacitance vs Drain-to-Source Voltage



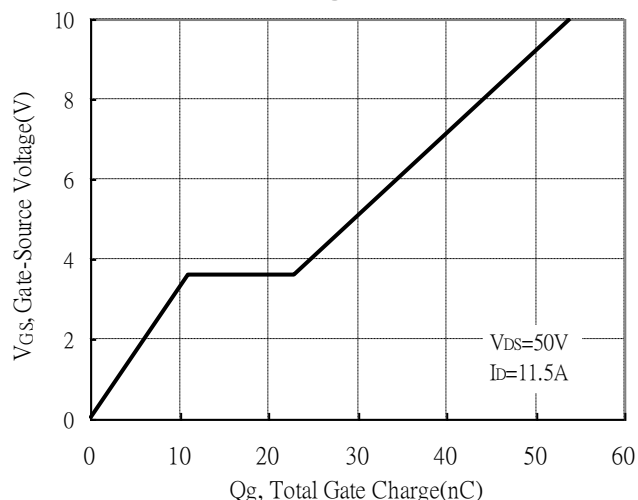
Threshold Voltage vs Junction Temperature



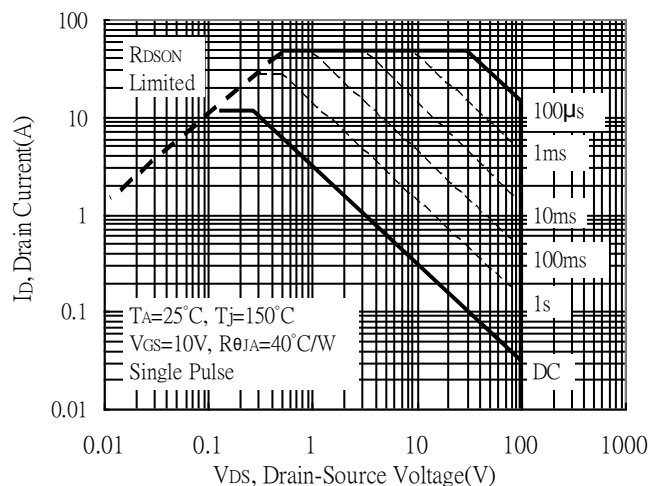
Forward Transfer Admittance vs Drain Current



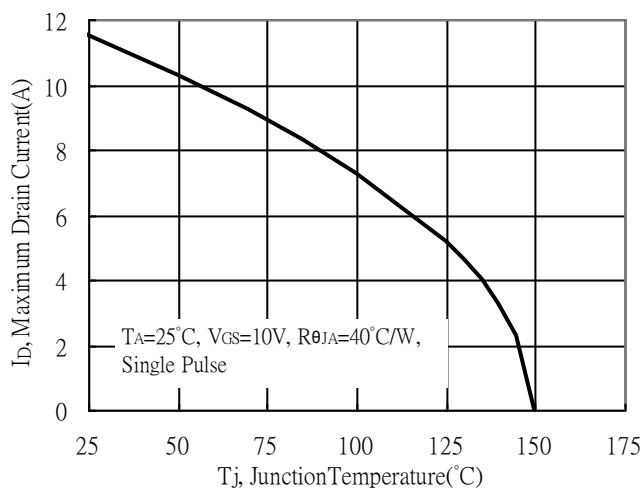
Gate Charge Characteristics



Maximum Safe Operating Area

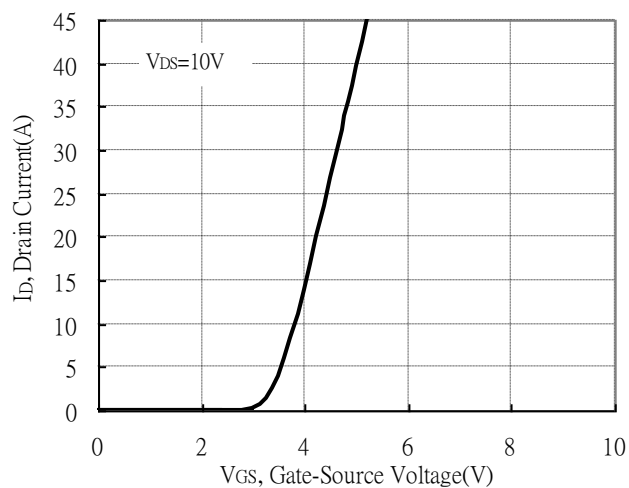


Maximum Drain Current vs Junction Temperature

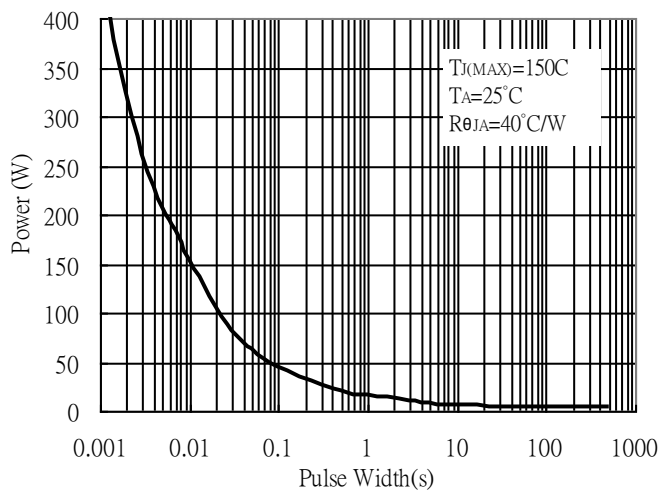


Typical Characteristics(Cont.)

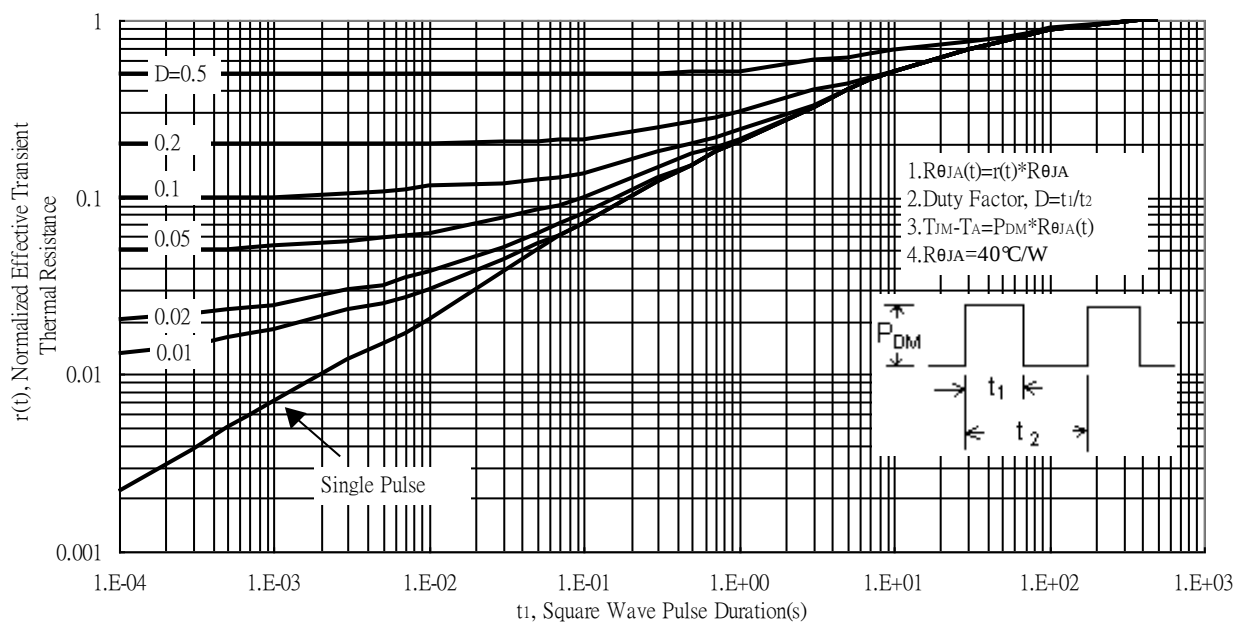
Typical Transfer Characteristics



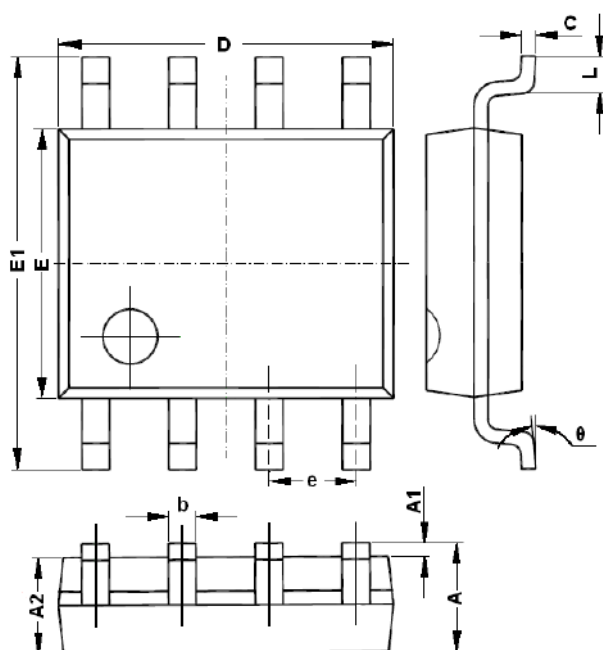
Single Pulse Maximum Power Dissipation



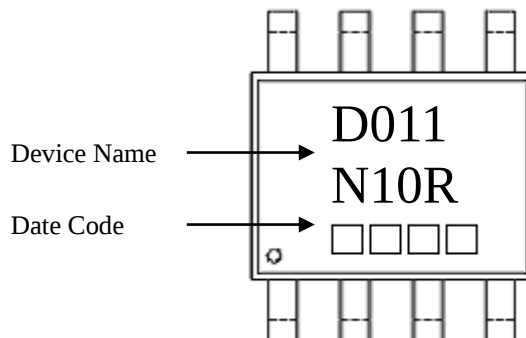
Transient Thermal Response Curves



SOP-8 Dimension



Marking:



Date Code(counting from left to right) :

1st code: year code, the last digit of Christian year

2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D

May→E, Jun→F, Jul→G, Aug→H, Sep→J,

Oct→K, Nov→L, Dec→M

3rd and 4th codes : production serial number, 01~99

8-Lead SOP-8 Plastic
 Package Code: Q8

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069	E	3.800	4.000	0.150	0.157
A1	0.100	0.250	0.004	0.010	E1	5.800	6.200	0.228	0.244
A2	1.350	1.550	0.053	0.061	e	1.270	(BSC)	0.050	(BSC)
b	0.330	0.510	0.013	0.020	L	0.400	1.270	0.016	0.050
c	0.170	0.250	0.006	0.010	θ	0	8°	0	8°
D	4.700	5.100	0.185	0.200					